QM3003G-VB Datasheet

P-Channel 35 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[d]	Q_g (Typ.)
- 35	0.040 at V_{GS} = - 10 V	- 6.2	9.8 nC
	0.048 at V_{GS} = - 4.5 V	- 5.1	

FEATURES

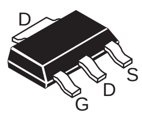
- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

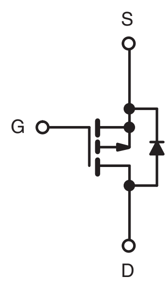
Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Load Switches, Adaptor Switch
  - Notebook PCs

SOT-223





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 35	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 6.2	A
	T_C = 70 °C		- 4.8	
	T_A = 25 °C		- 4.5[a, b]	
	T_A = 70 °C		- 3.4[a, b]	
Pulsed Drain Current		I_{DM}	- 20	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 3.5	
	T_A = 25 °C		- 2.1[a, b]	
Avalanche Current	L = 0.1 mH	I_{AS}	- 10	
Single-Pulse Avalanche Energy		E_{AS}	5	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	4.2	W
	T_C = 70 °C		2.7	
	T_A = 25 °C		2.5[a, b]	
	T_A = 70 °C		1.6[a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a, c]	t ≤ 10 s	R_{thJA}	40	50	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	24	30	

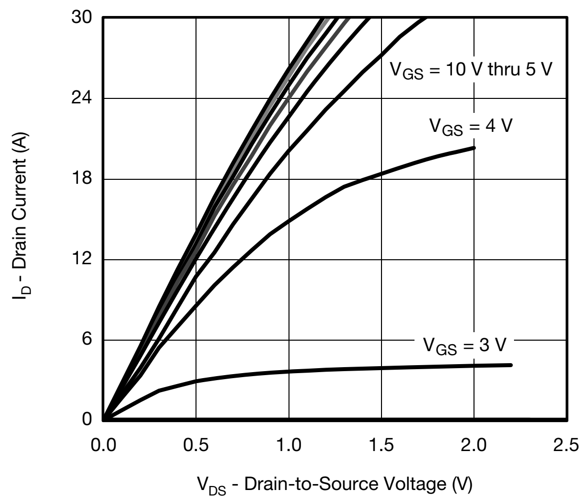
Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Maximum under steady state conditions is 85 °C/W.
d. Based on T_C = 25 °C.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 35			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 42		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.6		- 1.8	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 35 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 35 V, V_{GS} = 0 V, T_J = 55 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ - 10 V, V_{GS} = - 10 V	- 10			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 5 A		0.040		Ω
		V_{GS} = - 4.5 V, I_D = - 4 A		0.048		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 5 A		14		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 20 V, V_{GS} = 0 V, f = 1 MHz		970		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			95		
Total Gate Charge	Q_g	V_{DS} = - 20 V, V_{GS} = - 10 V, I_D = - 5 A		23	35	nC
		V_{DS} = - 20 V, V_{GS} = - 4.5 V, I_D = - 5 A		9.8	16	
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			5.2		
Gate Resistance	R_g	f = 1 MHz	1.0	5.5	11	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 20 V, R_L = 4 Ω $I_D \cong$ - 5 A, V_{GEN} = - 10 V, R_g = 1 Ω		7	14	ns
Rise Time	t_r			12	24	
Turn-Off DelayTime	$t_{d(off)}$			30	60	
Fall Time	t_f			9	18	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 20 V, R_L = 4 Ω $I_D \cong$ - 5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		44	80	
Rise Time	t_r			33	60	
Turn-Off DelayTime	$t_{d(off)}$			28	55	
Fall Time	t_f			13	25	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 3.5	A
Pulse Diode Forward Current	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	I_S = - 2 A, V_{GS} = 0 V		- 0.76	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 2 A, dI/dt = 100 A/µs, T_J = 25 °C		27	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}			19	35	nC
Reverse Recovery Fall Time	t_a			14		ns
Reverse Recovery Rise Time	t_b			13		

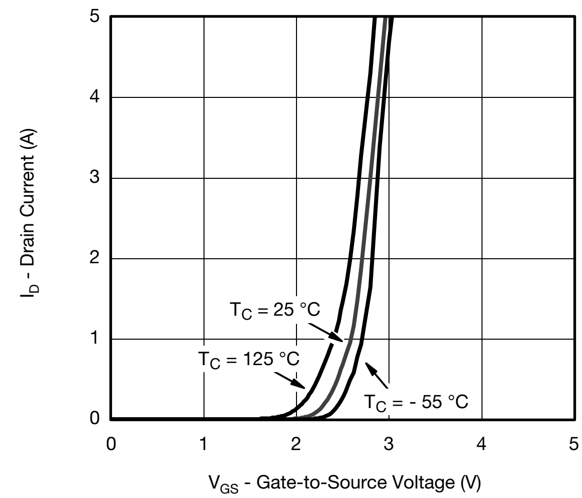
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

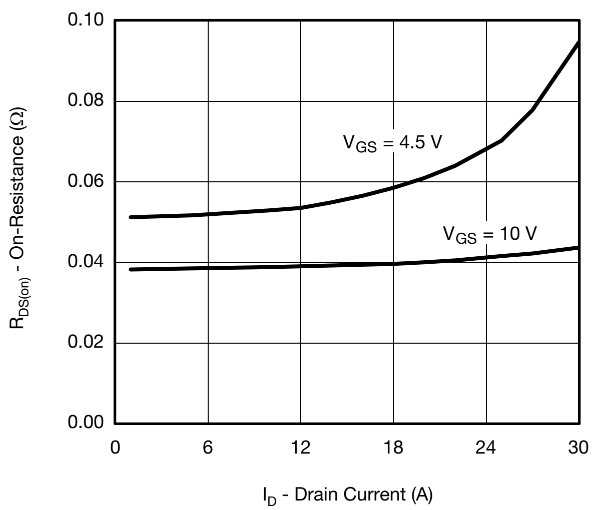
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



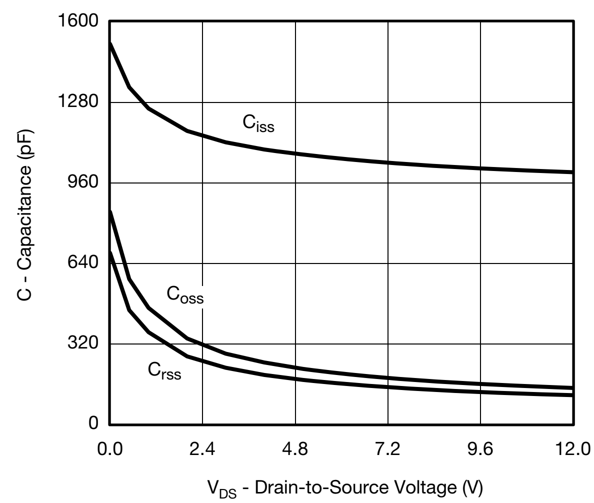
Output Characteristics



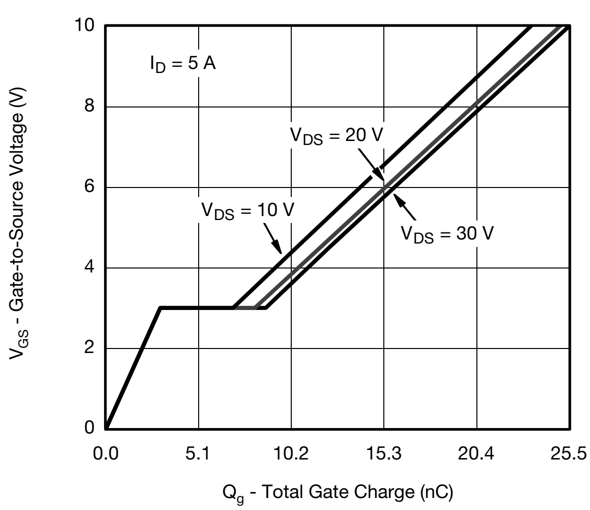
Transfer Characteristics



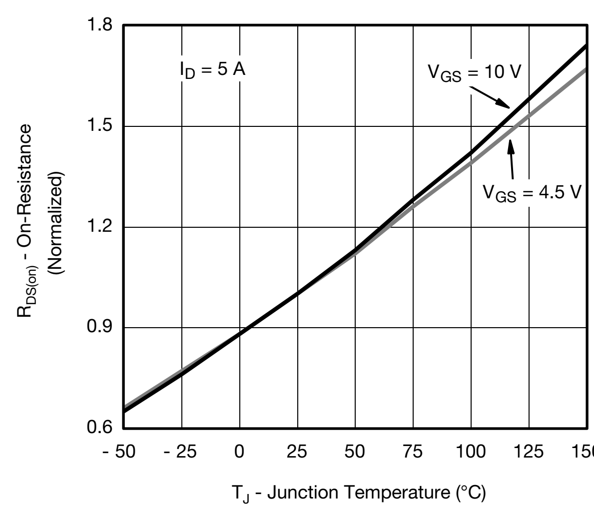
On-Resistance vs. Drain Current



Capacitance

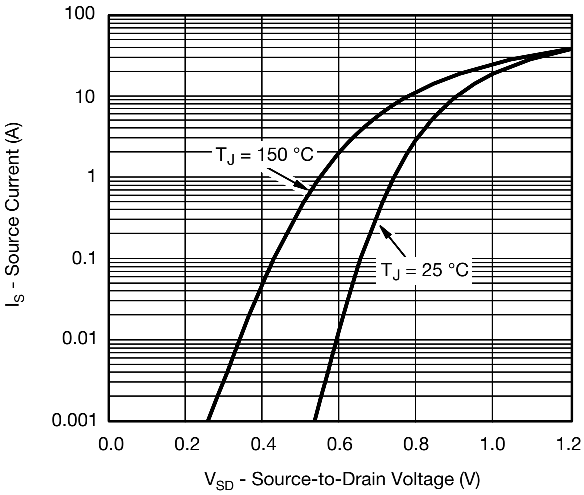


Gate Charge

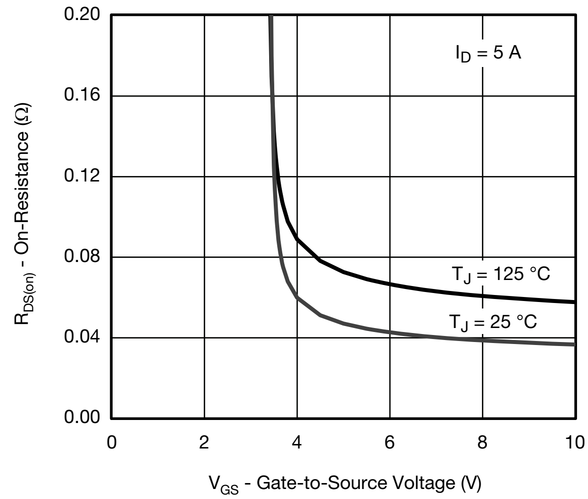


On-Resistance vs. Junction Temperature

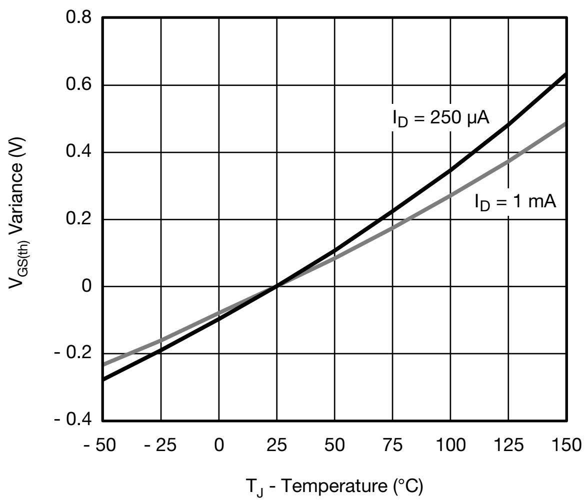
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



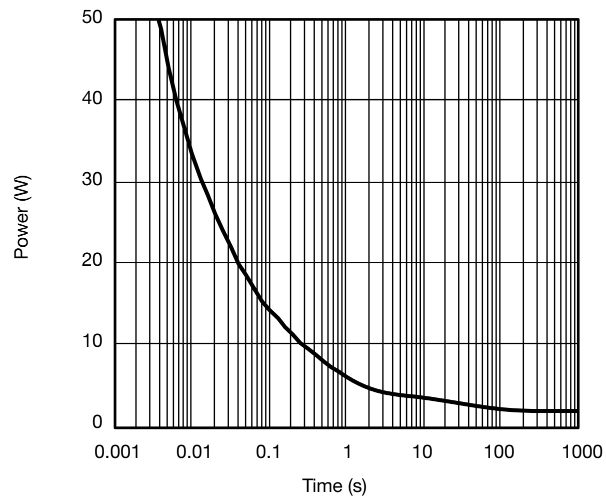
Source-Drain Diode Forward Voltage



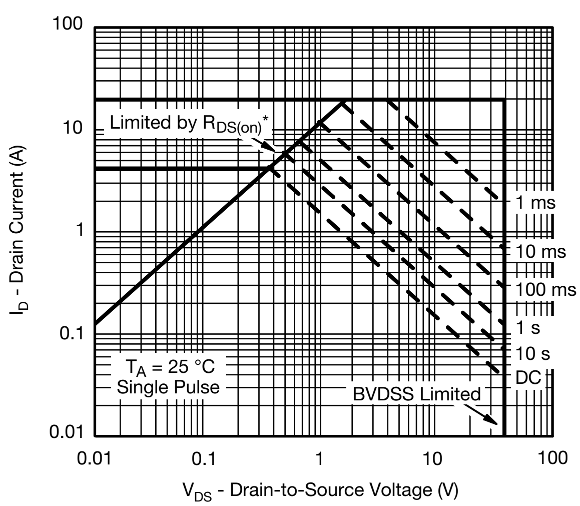
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



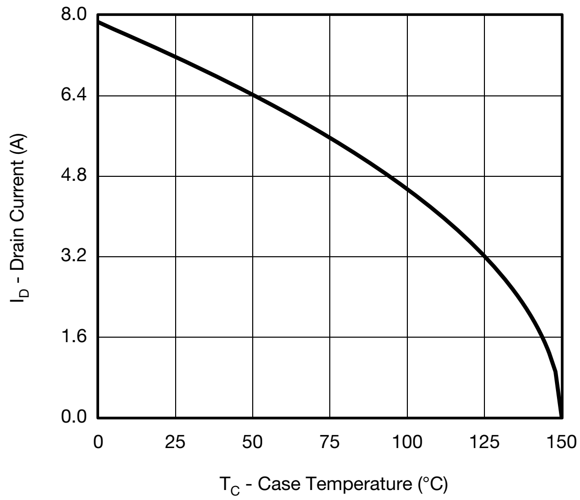
Single Pulse Power, Junction-to-Ambient



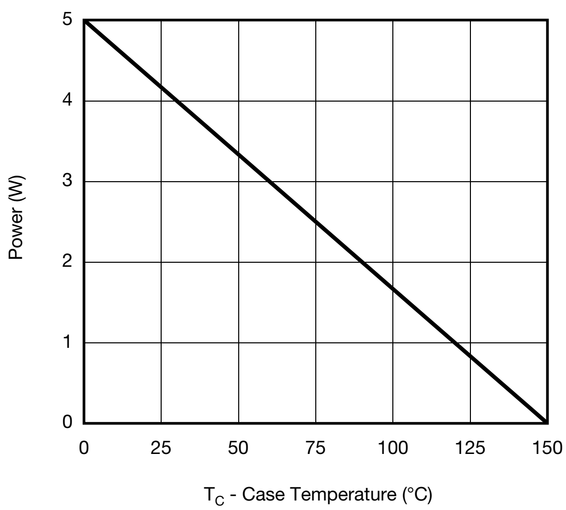
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

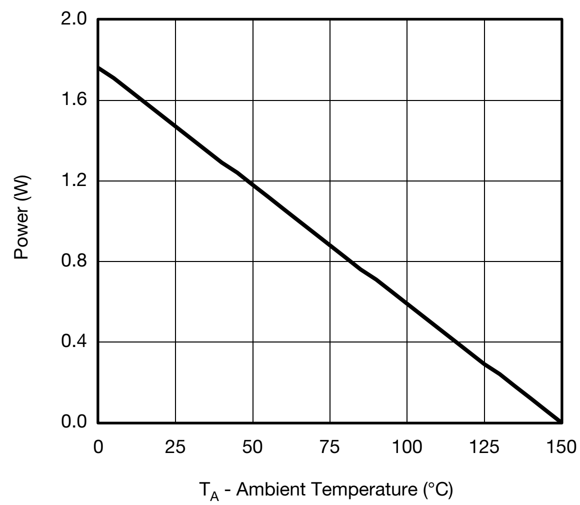
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



Power, Junction-to-Foot

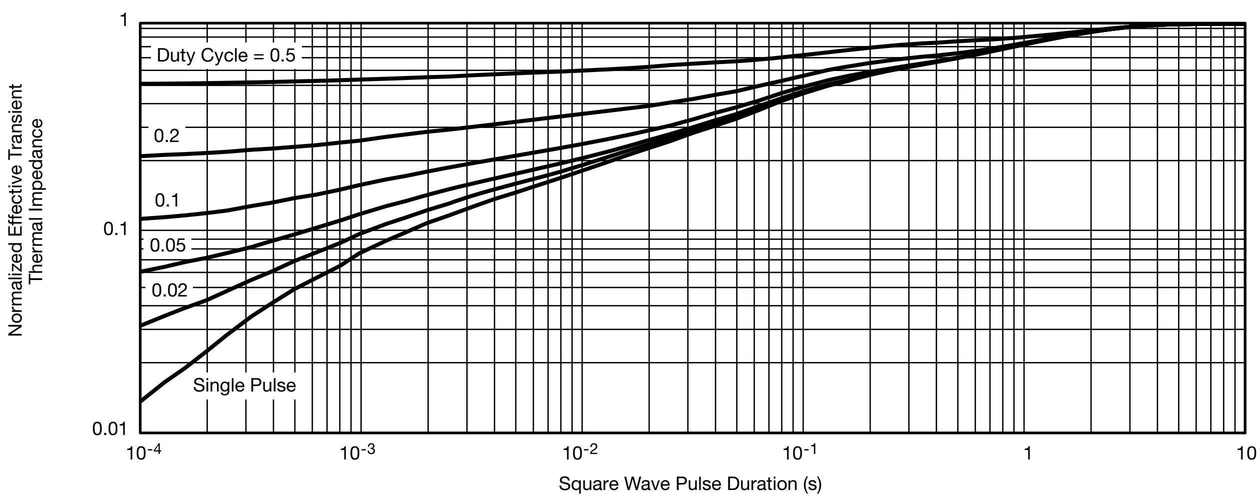


Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

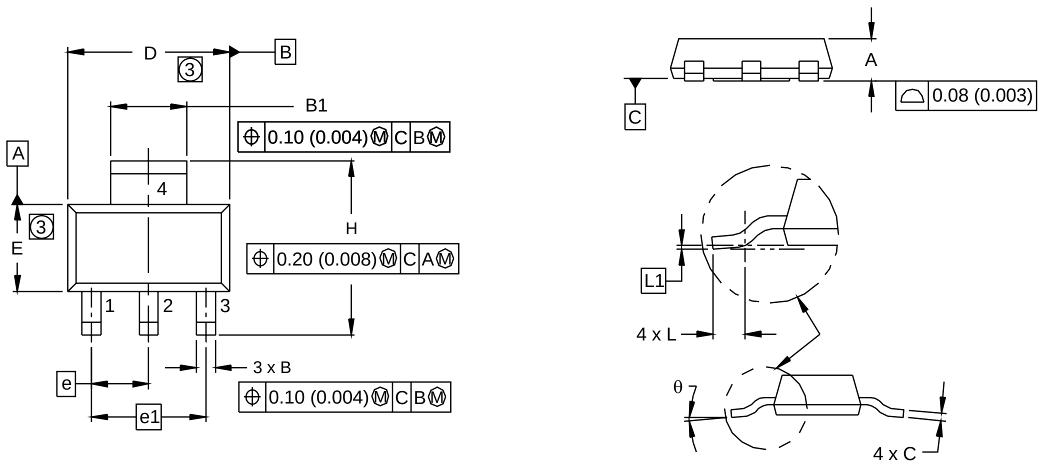
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-223 (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10'	-	10'
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.

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